

# IRL3202SPbF

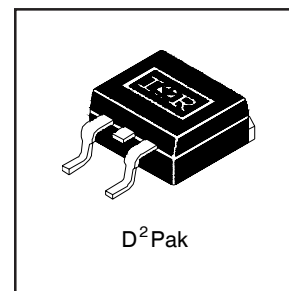
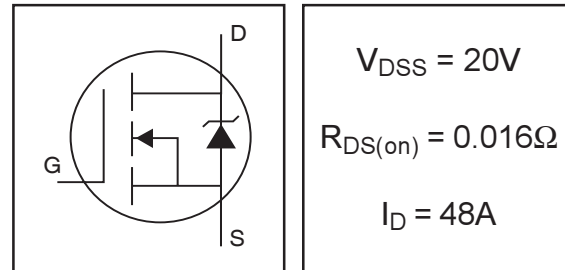
HEXFET® Power MOSFET

- Advanced Process Technology
- Surface Mount
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching
- Lead-Free

## Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters in the PC environment. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}$ Ⓞ	48	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}$ Ⓞ	30	
$I_{DM}$	Pulsed Drain Current Ⓞ Ⓞ	190	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	69	W
	Linear Derating Factor	0.56	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$V_{GSM}$	Gate-to-Source Voltage (Start Up Transient, $t_p = 100\mu\text{s}$ )	14	V
$E_{AS}$	Single Pulse Avalanche EnergyⓄ Ⓞ	270	mJ
$I_{AR}$	Avalanche CurrentⓄ	29	A
$E_{AR}$	Repetitive Avalanche EnergyⓄ	6.9	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ Ⓞ Ⓞ	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient ( PCB Mounted, steady-state)**	---	40	

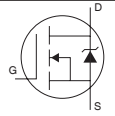
# IRL3202SPbF

International  
**IR** Rectifier

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA <sup>④</sup>
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.019	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 29A <sup>④</sup>
		—	—	0.016		V <sub>GS</sub> = 7.0V, I <sub>D</sub> = 29A <sup>④</sup>
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.70	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	28	—	—	S	V <sub>DS</sub> = 16V, I <sub>D</sub> = 29A <sup>④</sup>
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 10V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -10V
Q <sub>g</sub>	Total Gate Charge	—	—	43	nC	I <sub>D</sub> = 29A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	12		V <sub>DS</sub> = 16V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	13		V <sub>GS</sub> = 4.5V, See Fig. 6 <sup>④⑤</sup>
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.8	—	ns	V <sub>DD</sub> = 10V
t <sub>r</sub>	Rise Time	—	100	—		I <sub>D</sub> = 29A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	63	—		R <sub>G</sub> = 9.5Ω, V <sub>GS</sub> = 4.5V
t <sub>f</sub>	Fall Time	—	82	—		R <sub>D</sub> = 0.3Ω, <sup>④⑤</sup>
L <sub>S</sub>	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C <sub>iss</sub>	Input Capacitance	—	2000	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	800	—		V <sub>DS</sub> = 15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	290	—		f = 1.0MHz, See Fig. 5 <sup>⑤</sup>

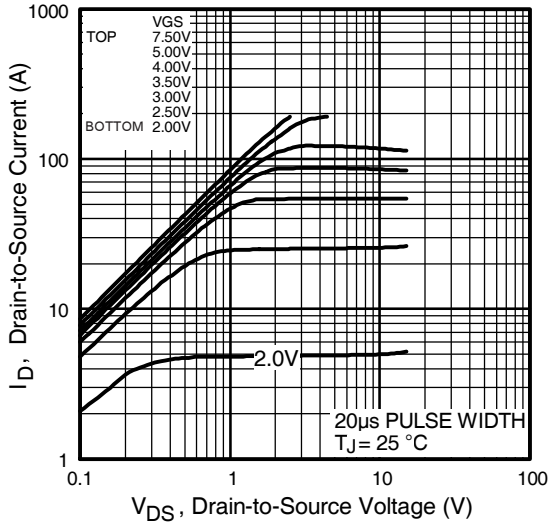
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	48	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) <sup>①⑤</sup>	—	—	190		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 29A, V <sub>GS</sub> = 0V <sup>④</sup>
t <sub>rr</sub>	Reverse Recovery Time	—	68	100	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 29A
Q <sub>rr</sub>	Reverse Recovery Charge	—	130	190	nC	di/dt = 100A/μs <sup>④⑤</sup>
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

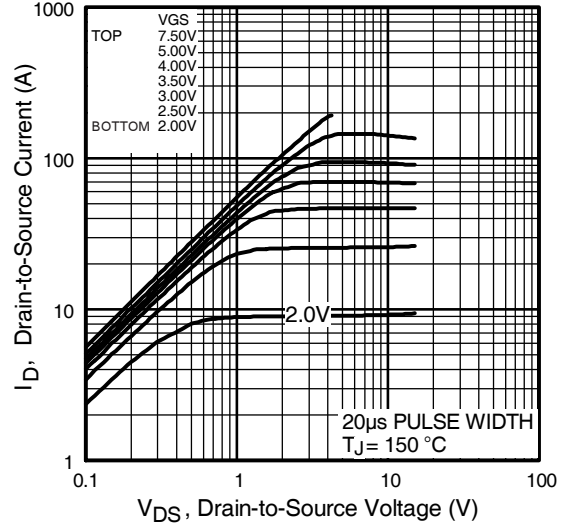
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting T<sub>J</sub> = 25°C, L = 0.64mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 29A.
- ③ I<sub>SD</sub> ≤ 29A, di/dt ≤ 63A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Uses IRL3202 data and test conditions

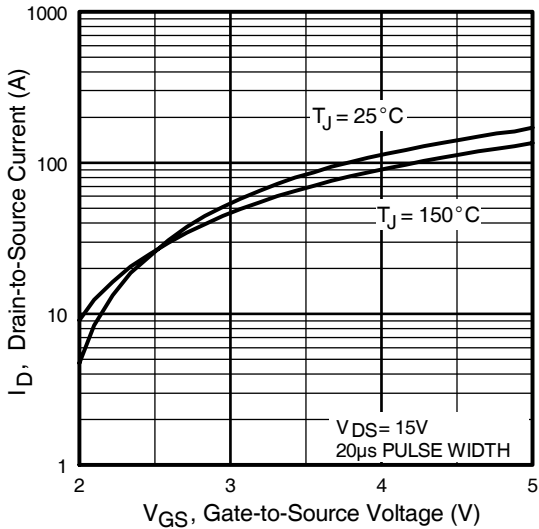
\*\* When mounted on FR-4 board using minimum recommended footprint.  
For recommended footprint and soldering techniques refer to application note #AN-994.



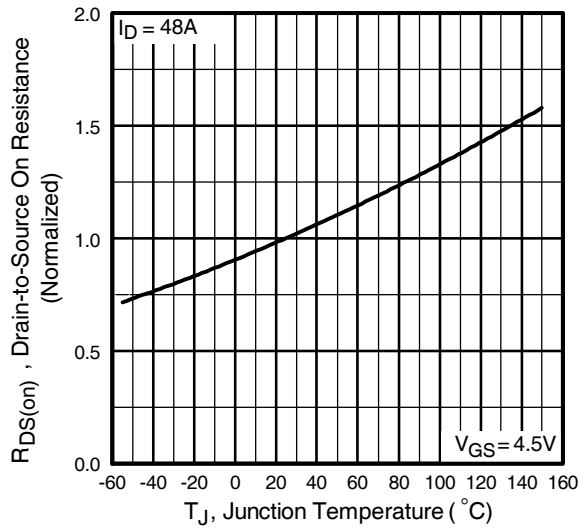
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

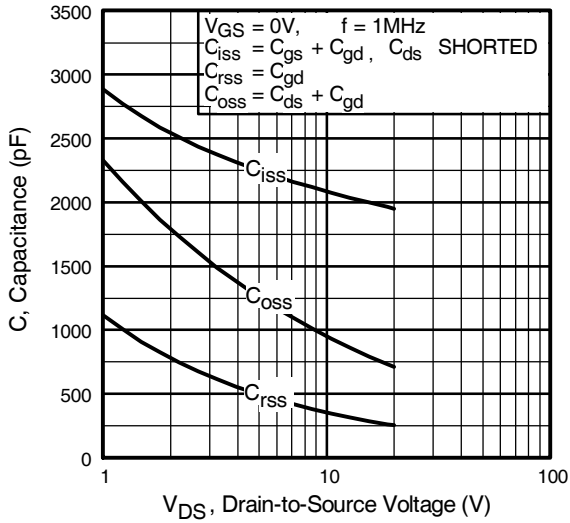


**Fig 3.** Typical Transfer Characteristics

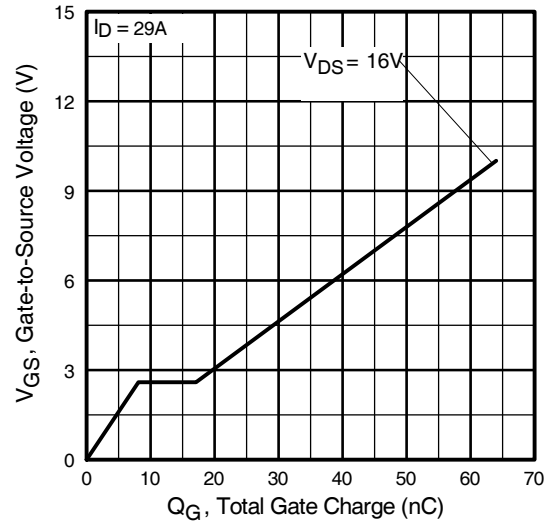


**Fig 4.** Normalized On-Resistance Vs. Temperature

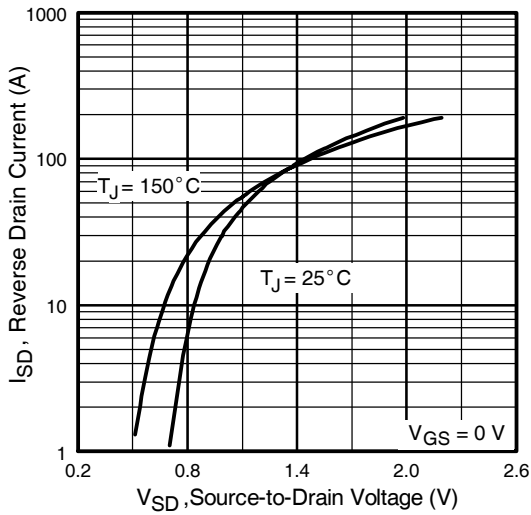
# IRL3202SPbF



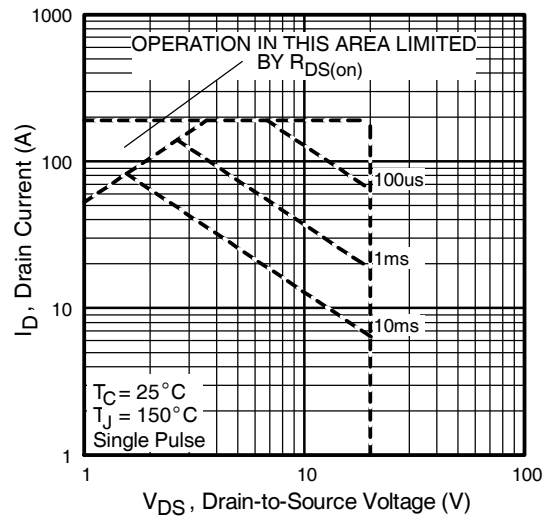
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



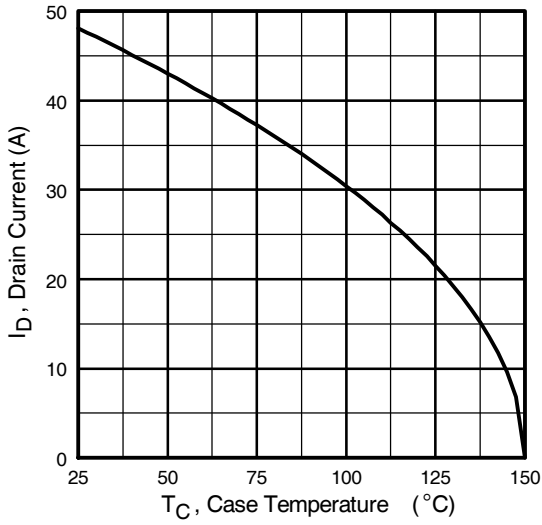
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



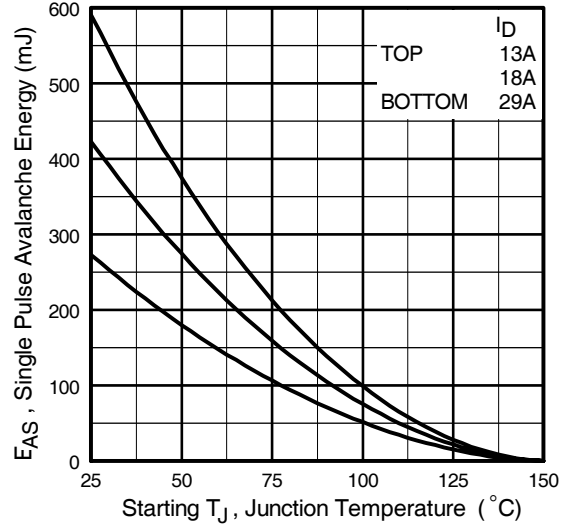
**Fig 7.** Typical Source-Drain Diode Forward Voltage



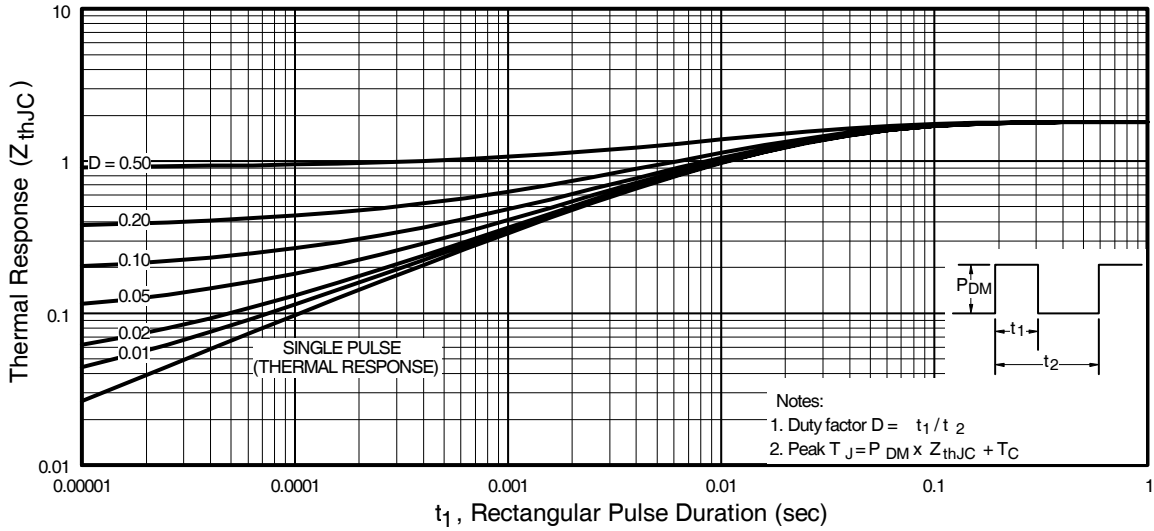
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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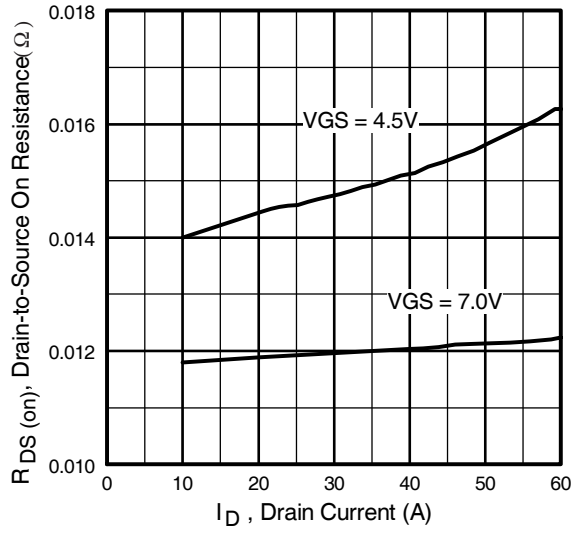


Fig 12. On-Resistance Vs. Drain Current

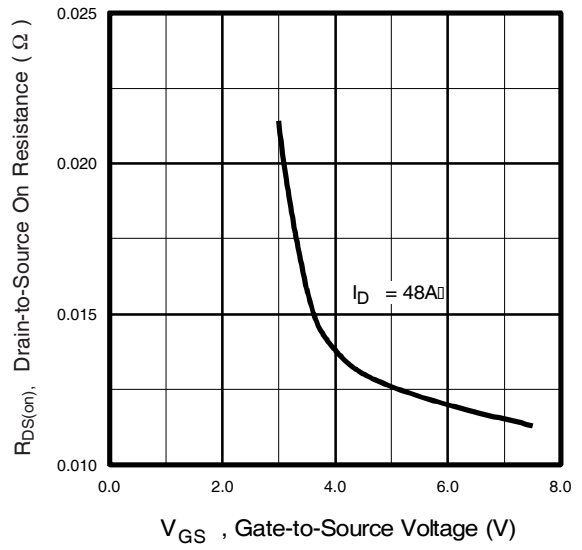
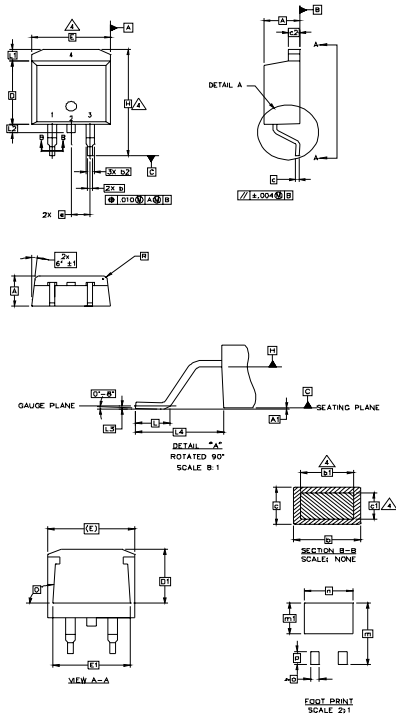


Fig 13. On-Resistance Vs. Gate Voltage

## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.78	.045	.070	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	4
c2	1.14	1.65	.045	.065	
D	8.51	9.65	.335	.380	3
D1	6.86		.270		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	1.27	1.65	.050	.065	
L2	1.27	1.78	.050	.070	
L3	0.25	BSC	.010	BSC	
L4	4.78	5.28	.188	.208	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
R	0.51	0.71	.020	.028	
θ	90°	93°	90°	93°	

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

#### IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

#### DIODES

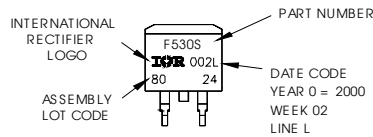
- 1.- ANODE \*
- 2, 4.- CATHODE
- 3.- ANODE

\* PART DEPENDENT.

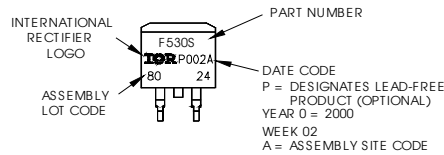
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRL3202 WITH  
LOT CODE 8024  
ASSEMBLED ON WW 02, 2000  
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line  
position indicates "Lead-Free"



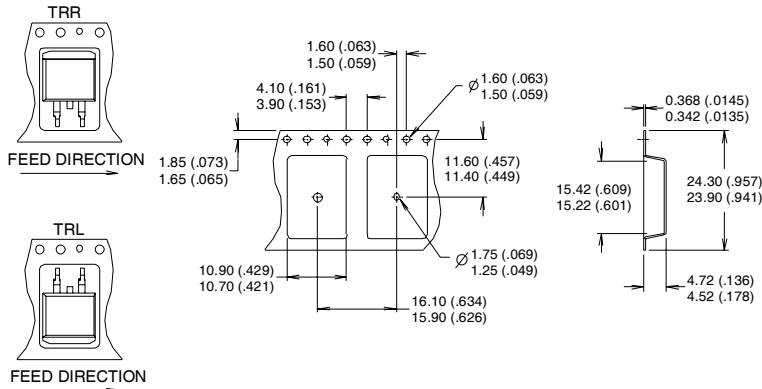
## OR



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## D<sup>2</sup>Pak Tape & Reel Information



- NOTES :
1. COMFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION MEASURED @ HUB.
  4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.

International  
**IR** Rectifier

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TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.12/04



Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>